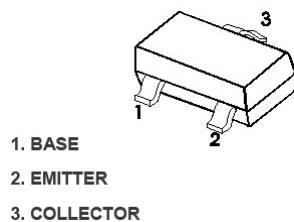


SOT-23**SOT-23 贴片塑封三极管  
SOT-23 Plastic-Encapsulate Transistors****Marking: 4D****特征 Features**

- 与 MMBTA44 配对; Complementary to MMBTA44
- 最大功率耗散 350mW; Power Dissipation of 350mW
- 高稳定性和可靠性。High Stability and High Reliability

**机械数据 Mechanical Data**

- 封装: SOT-23 封装 SOT-23 Small Outline Plastic Package
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

**极限值和温度特性(TA = 25°C 除非另有规定)****Maximum Ratings & Thermal Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	V <sub>CBO</sub>	-400	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-400	V
Emitter -Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current-Continuous	I <sub>c</sub>	-200	mA
Collector Power Dissipation	P <sub>c</sub>	350	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~+150	°C
Thermal resistance From junction to ambient	R <sub>θJA</sub>	357	°C/W

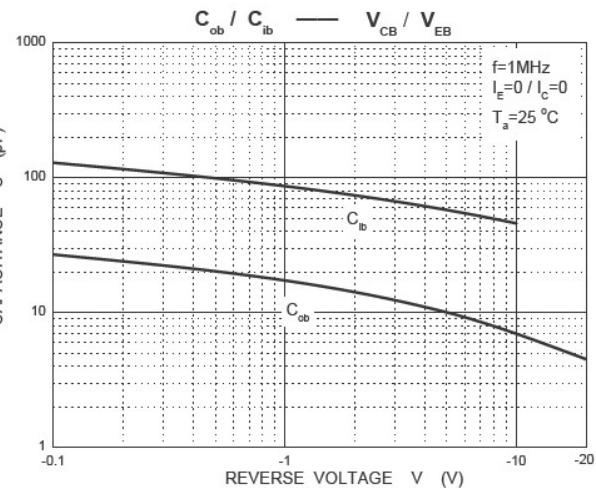
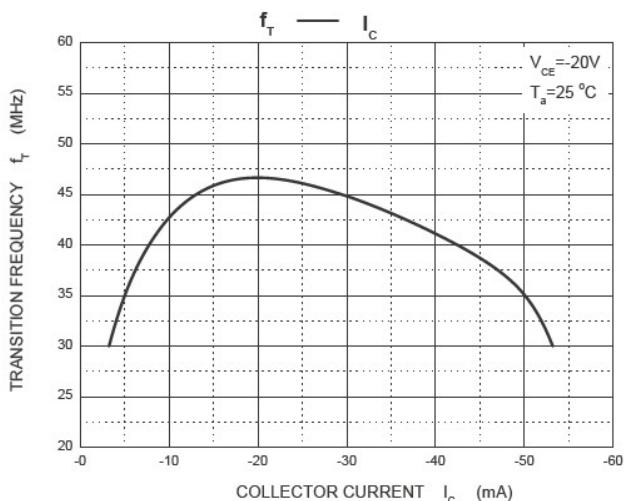
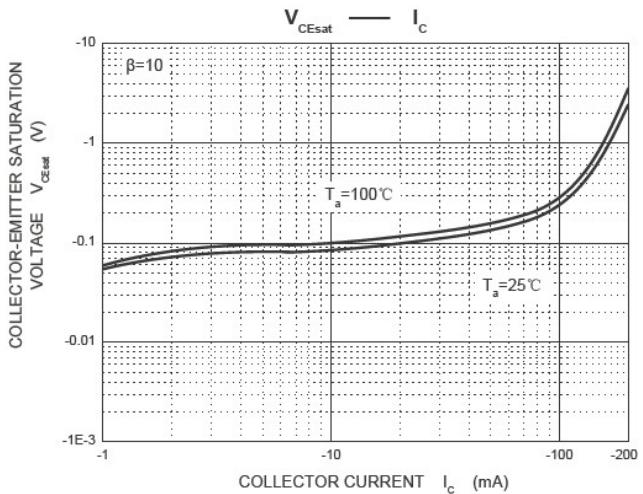
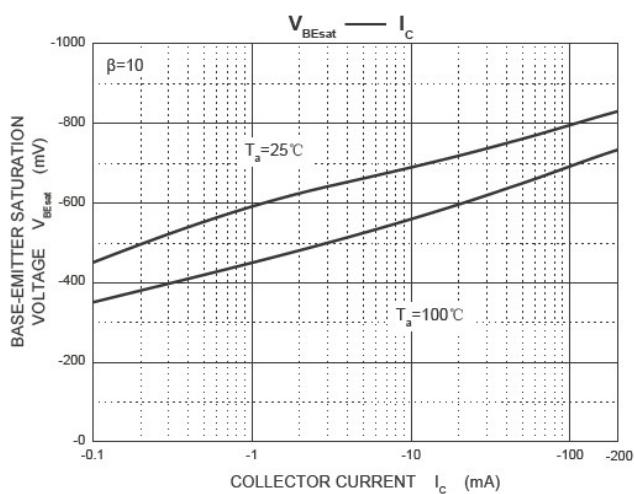
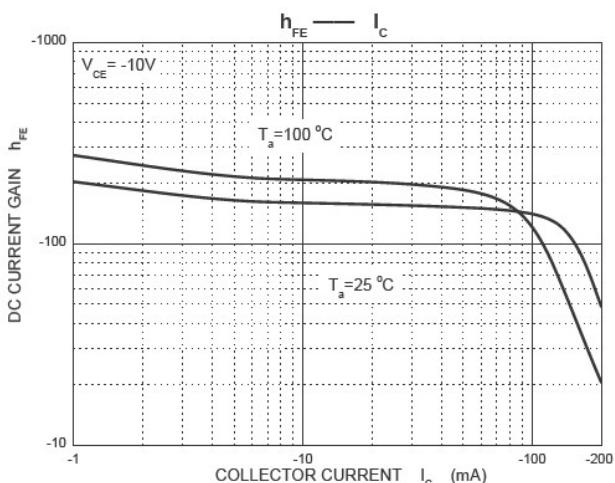
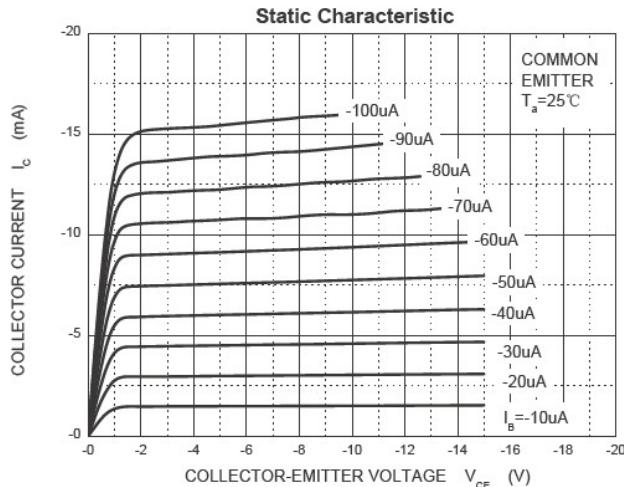
**电特性 (TA = 25°C 除非另有规定)****Electrical Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified).

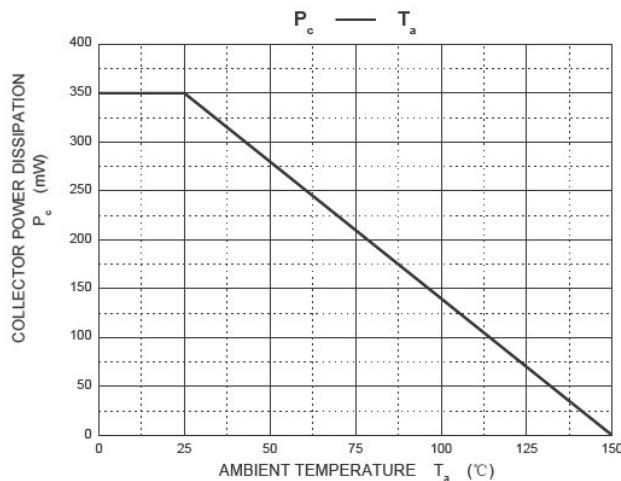
参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>c</sub> =-100uA, I <sub>e</sub> =0	-400		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub> *	I <sub>c</sub> =-1mA, I <sub>b</sub> =0	-400		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>e</sub> =-100uA, I <sub>c</sub> =0	-5		V
Collector cut-off current	I <sub>cbo</sub>	V <sub>cb</sub> =-400V, I <sub>e</sub> =0		-100	nA
Collector cut-off current	I <sub>ceo</sub>	V <sub>ce</sub> =-400V, I <sub>e</sub> =0		-5	uA
Emitter cut-off current	I <sub>ebo</sub>	V <sub>eb</sub> =-4V, I <sub>c</sub> =0		-100	nA
DC current gain	h <sub>FE(1)</sub> *	V <sub>ce</sub> =-10V, I <sub>c</sub> =-10mA	80	300	
	h <sub>FE(2)</sub> *	V <sub>ce</sub> =-10V, I <sub>c</sub> =-1mA	70		
	h <sub>FE(3)</sub> *	V <sub>ce</sub> =-10V, I <sub>c</sub> =-50mA	40		
	h <sub>FE(4)</sub> *	V <sub>ce</sub> =-10V, I <sub>c</sub> =-100mA	40		
Collector-emitter saturation voltage	V <sub>ce(sat)</sub> *	I <sub>c</sub> =-10mA, I <sub>b</sub> =-1mA		-0.20	V
	V <sub>ce(sat)</sub> *	I <sub>c</sub> =-50mA, I <sub>b</sub> =-5mA		-0.30	V
Base -emitter saturation voltage	V <sub>be(sat)</sub> *	I <sub>c</sub> =-10mA, I <sub>b</sub> =-1mA		-0.75	V
Transition frequency	f <sub>t</sub>	V <sub>ce</sub> =-20V, I <sub>c</sub> =10mA, f=30MHz	50		MHz

\*Pulse test: pulse width≤300us, duty cycle≤2. 0%

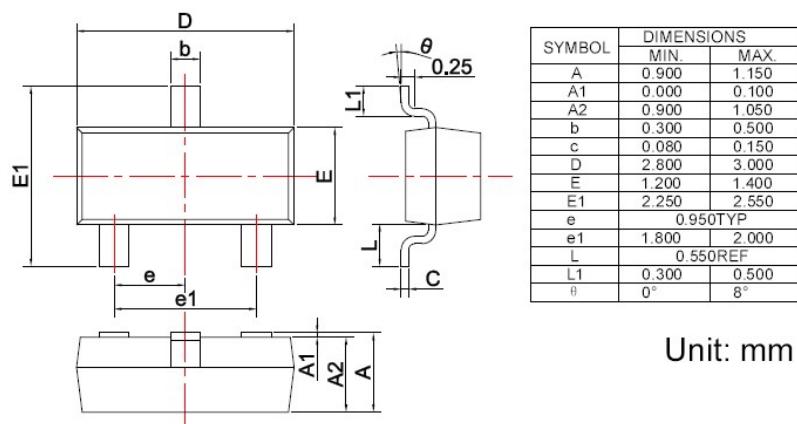
# MMBTA94

## Typical characteristics



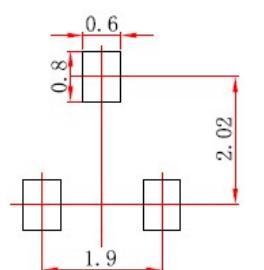


### SOT-23 PACKAGE OUTLINE Plastic surface mounted package



### 焊盘设计参考 Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



#### Note:

1. Controlling dimension: In millimeters.
2. General tolerance:  $\pm 0.05$ mm.
3. The pad layout is for reference purposes only.

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